

**SANYO**

No.3817

**2SJ232**

P-Channel MOS Silicon FET

Very High-Speed  
Switching Applications**Features**

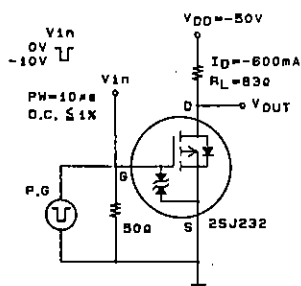
- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Its height onboard is 9.5mm.
- Meets radial taping.

**Absolute Maximum Ratings at Ta = 25°C**

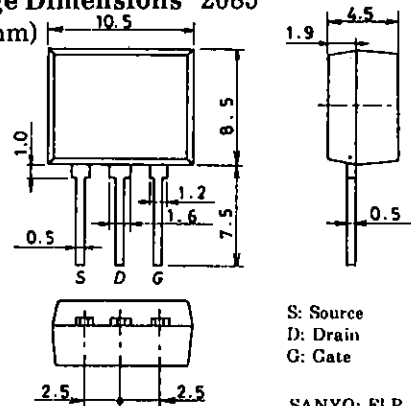
			unit
Drain to Source Voltage	$V_{DS}$	-100	V
Gate to Source Voltage	$V_{GS}$	±15	V
Drain Current(DC)	$I_D$	-1.2	A
Drain Current(Pulse)	$I_{DP}$	-4.8	A
Allowable Power Dissipation	$P_D$	1.5	W
Channel Temperature	$T_{ch}$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

 $PW \leq 10\mu s$ , duty cycle  $\leq 1\%$ **Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-100			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	±15			V
Zero Gate Voltage	$I_{DSS}$	$V_{DS} = -100V, V_{GS} = 0$			-100	$\mu A$
Drain Current						
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0$			±10	$\mu A$
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -600mA$	0.9	1.6		S
Static Drain to Source	$R_{DS(on)}$	$I_D = -600mA, V_{GS} = -10V$		0.7	0.95	$\Omega$
on State Resistance	$R_{DS(on)}$	$I_D = -600mA, V_{GS} = -4V$		0.95	1.3	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = -20V, f = 1MHz$		380		pF
Output Capacitance	$C_{oss}$	$V_{DS} = -20V, f = 1MHz$		100		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = -20V, f = 1MHz$		20		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		12		ns
Rise Time	$t_r$	"		14		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		85		ns
Fall Time	$t_f$	"		40		ns
Diode Forward Voltage	$V_{SD}$	$I_S = -1.2A, V_{GS} = 0$	-1.0	-1.5		V

**Switching Time Test Circuit****Package Dimensions 2085**

(unit : mm)

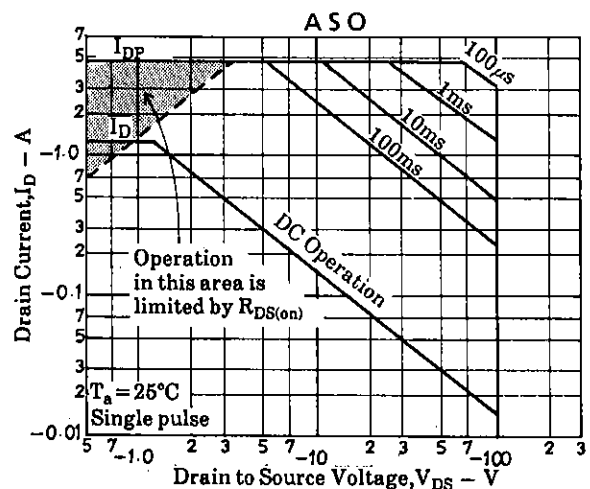
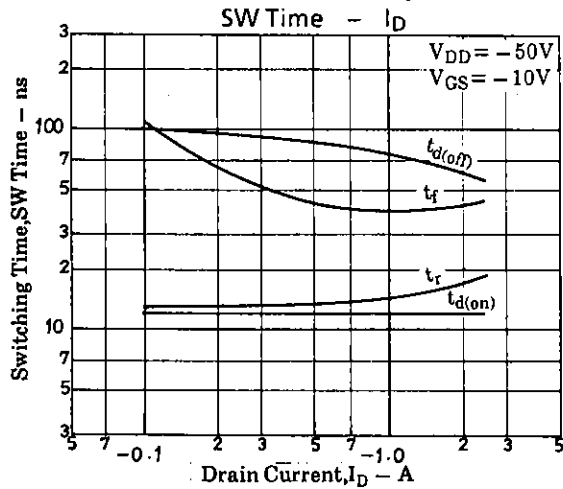
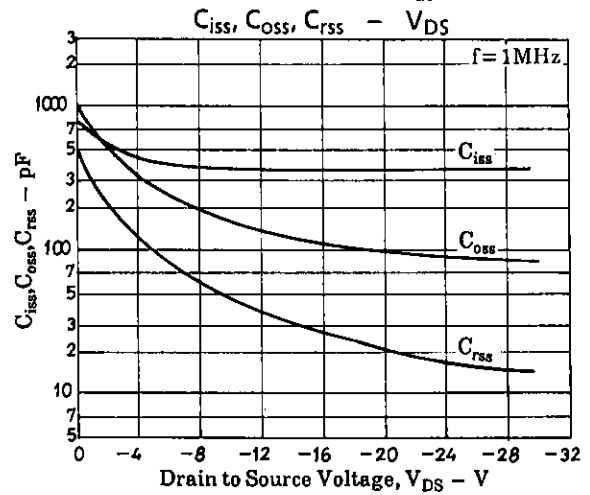
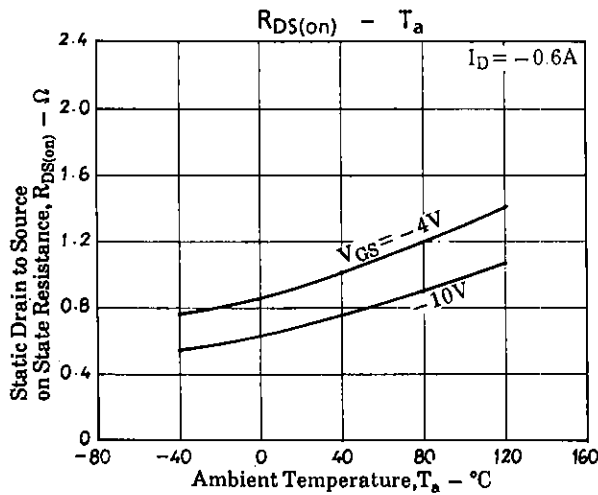
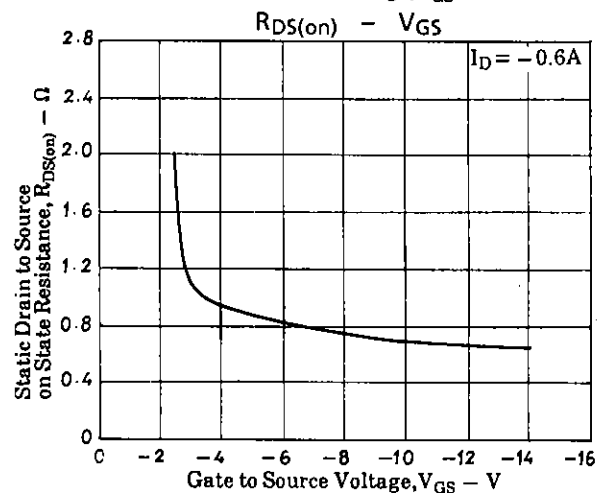
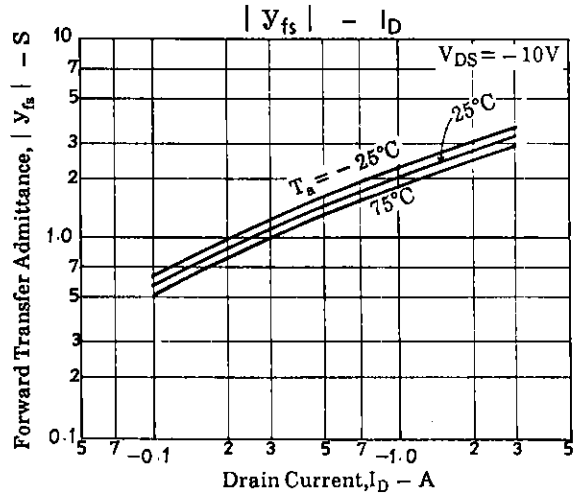
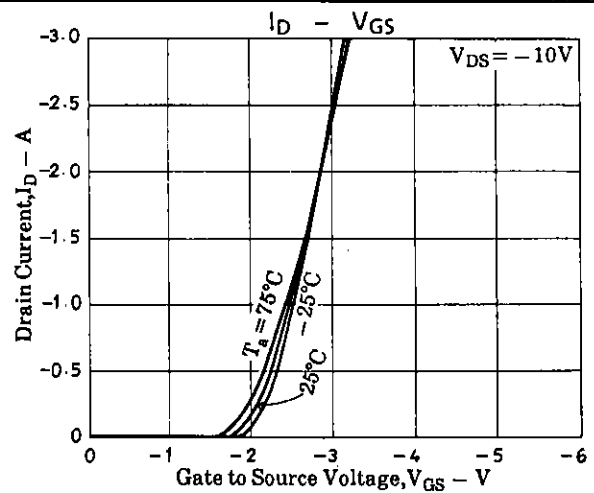
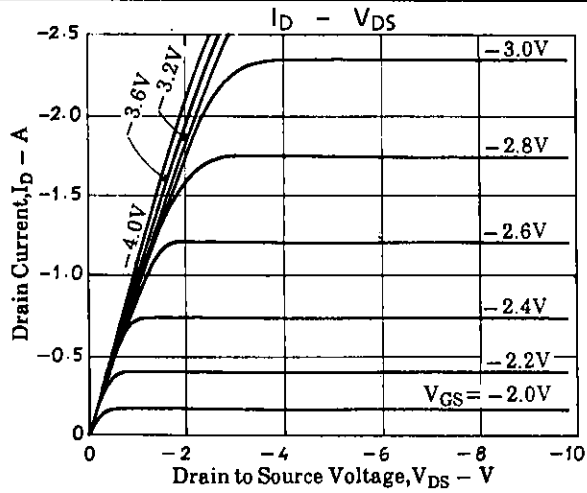
S: Source  
D: Drain  
G: Gate

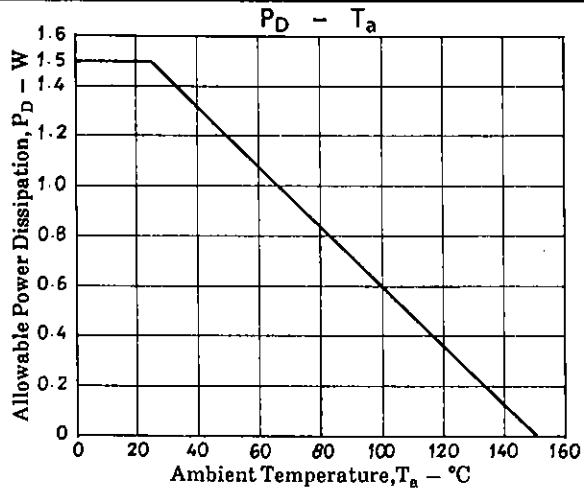
SANYO: FLP

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